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**Product Data Sheet**

**Ultraviolet LED Chip**

**EOLC-380-34**

Rev. 01, 2014

Radiation	Type	Electrodes
UV	InGaN/GaN	P + N up

	Description
	<ul style="list-style-type: none"> <li>- chip size: 330 μm x 275 μm (13 x 11 mil)</li> <li>- chip thickness: 90 ± 20 μm</li> <li>- P- bonding pad electrode: Ø85 μm, thickness 3.5 ± 0.35 μm, Au</li> <li>- N- bonding pad electrode: Ø85 μm, thickness 3.5 ± 0.35 μm, Au</li> </ul>

**Maximum Ratings**

T<sub>amb</sub>= 25°C, unless otherwise specified

Parameter	Test cond.	Symbol	Min	Typ	Max	Unit
Forward current (DC)		I <sub>F</sub>			20	mA

**Optical and Electrical Characteristics**

T<sub>amb</sub>= 25°C, unless otherwise specified

Parameter	Test cond.	Symbol	Min	Typ	Max	Unit
Forward voltage	I <sub>F</sub> =20 mA	V <sub>F</sub>	3.3	3.4	3.5	V
Reverse current	V <sub>R</sub> =5 V	I <sub>R</sub>			0.5	μA
Peak wavelength	I <sub>F</sub> =20 mA	λ <sub>p</sub>		380	382.5	nm
Radiant intensity	I <sub>F</sub> =20 mA	I <sub>e</sub>	14	15	15.5	mW/sr

**Packing**

Chips on adhesive film with wire-bond side top

Art. No. 111 024



We reserve the right to make changes to improve technical design and may do so without further notice. Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer.